

The oblique Hanle effect in graphene: A novel approach to determine spin lifetime anisotropy

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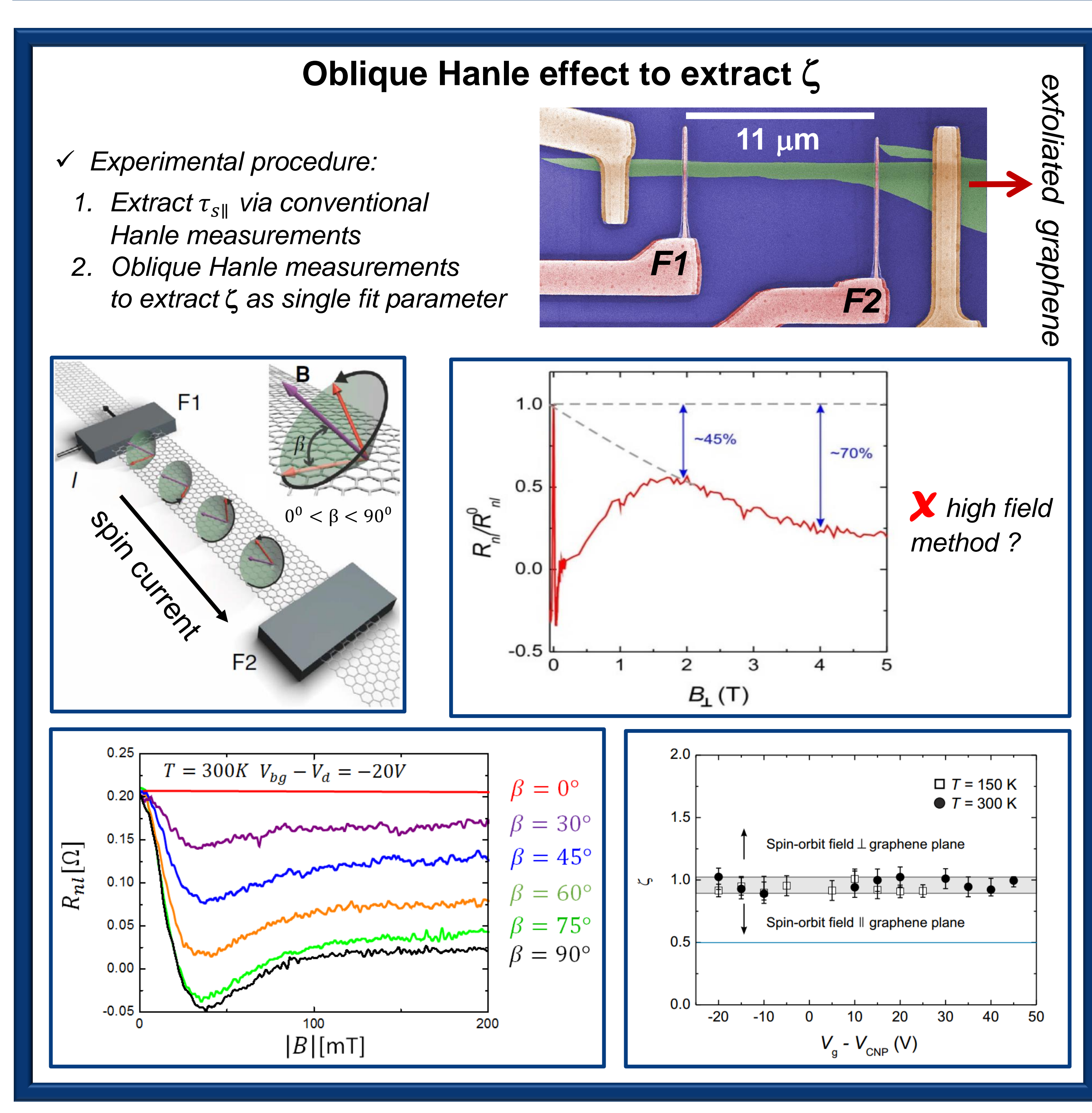
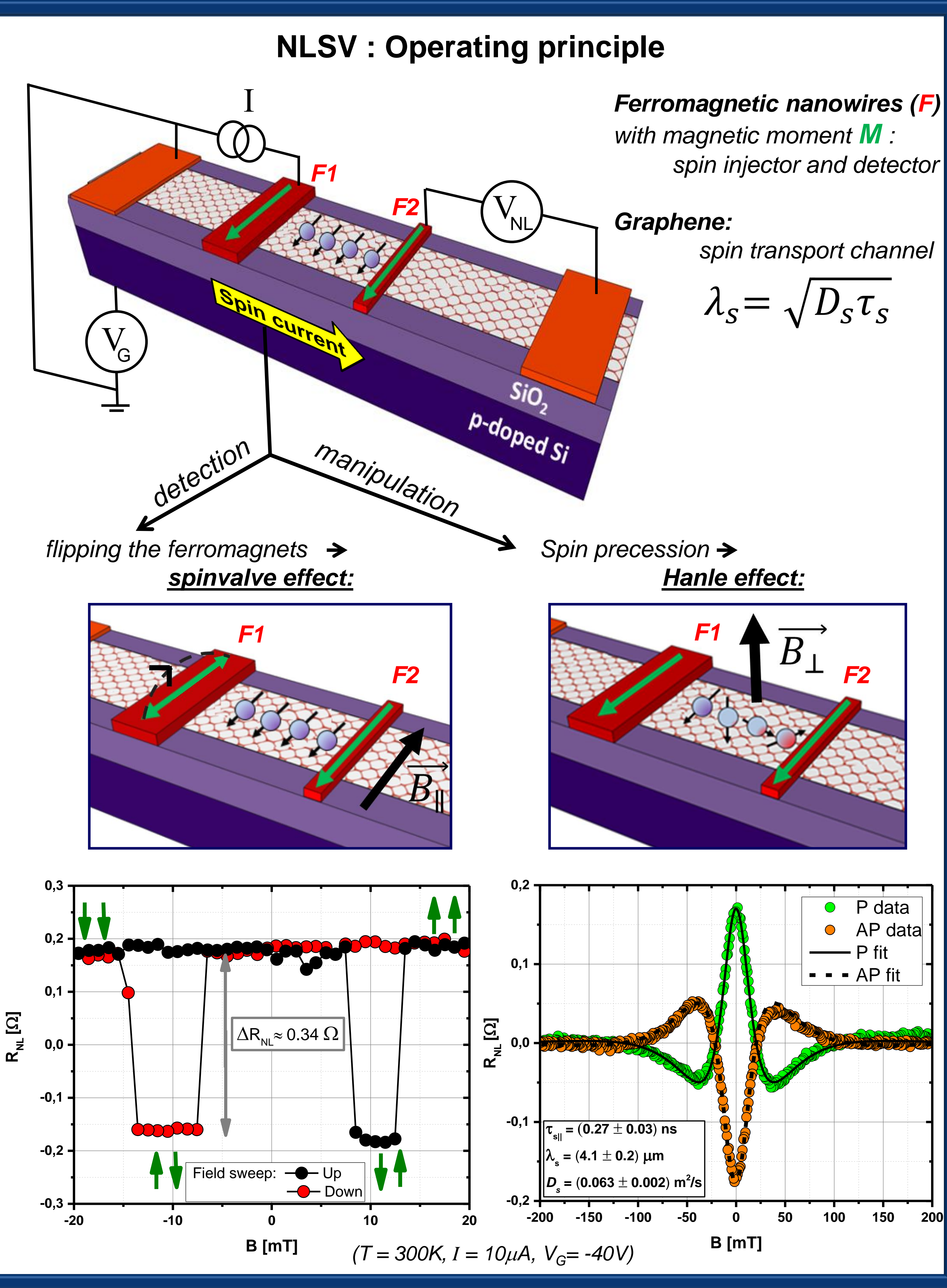
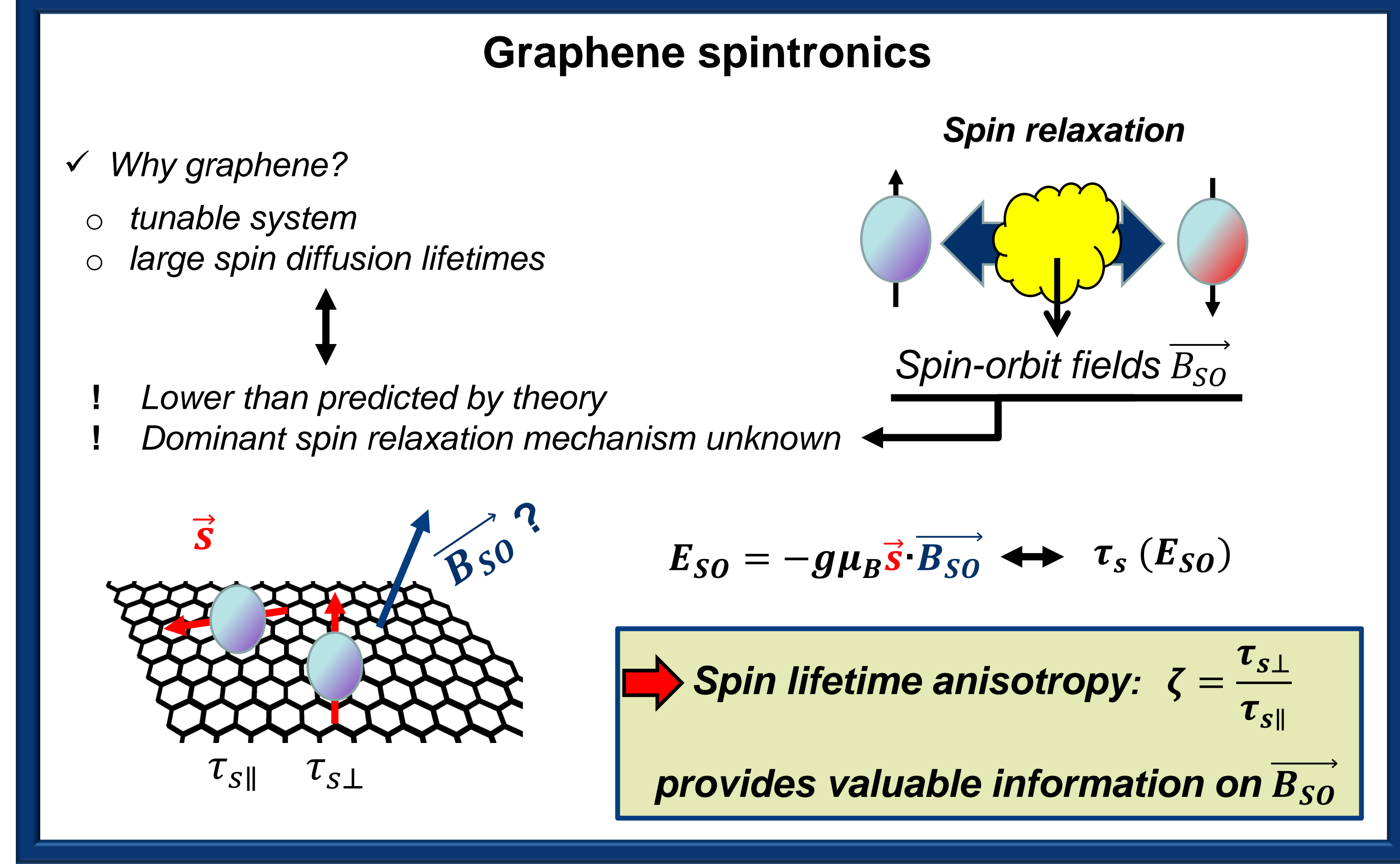
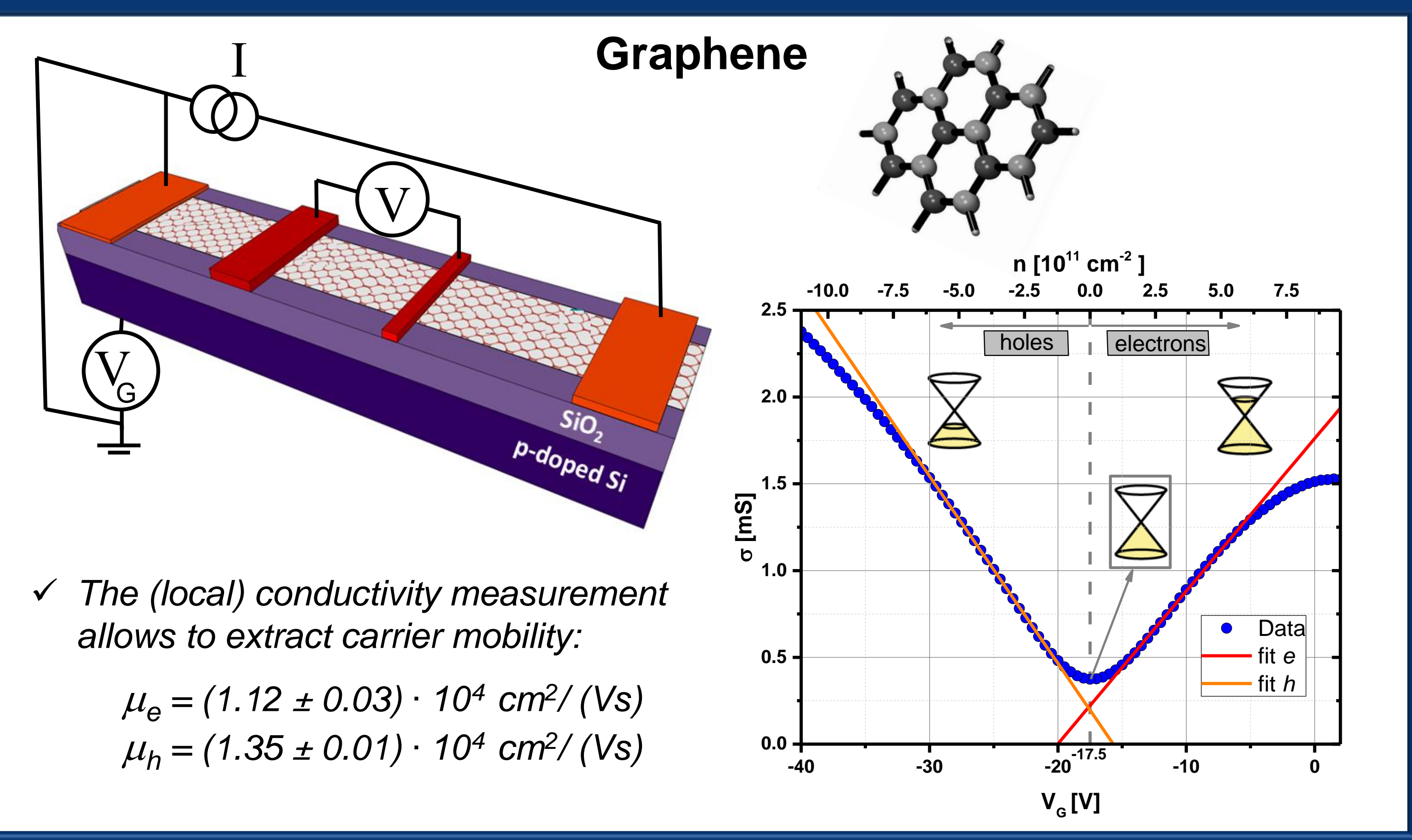
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Abstract

Spintronics make use of the spin degree of freedom of the electron in addition to (or instead of) its charge. **Graphene**, a true two-dimensional material consisting of a hexagonal lattice of carbon atoms, presents itself as an excellent material to transport spin currents since it exhibits long spin lifetimes. However, the main microscopic mechanisms for **spin relaxation** in graphene, which limit the spin lifetime, remain elusive. A key property to solve this puzzle is the **spin lifetime anisotropy** ζ , which is the ratio of the in-plane and out-of-plane spin lifetimes [1]. In previous reports [2], the spin lifetime anisotropy has been determined by spin transport measurements with large magnetic fields (>1T) applied perpendicular to the graphene plane, rendering it useless at low carrier densities. With the use of **non-local lateral spinvalves (NLSV)**, we demonstrate a conceptually new approach to extract ζ by performing spin precession measurement at low fields ($\sim 0.1T$) [3], overcoming the aforementioned limitation.



Conclusions and outlook

- ✓ The spin lifetime anisotropy ζ is important to unravel the spin relaxation mechanisms in graphene, and other 2D materials in general.
- ✓ We demonstrated a reliable approach to determine ζ using spin precession measurements. In our samples we find $\zeta \sim 1$, hinting to \vec{B}_{SO} due to random impurities.
- ✓ Further implementation of this method in other samples (e.g. other graphene sources, different substrates, heterostructures, adatoms,...) leads to a better understanding and better controllability of spin-orbit fields and spin relaxation in graphene.

References:

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